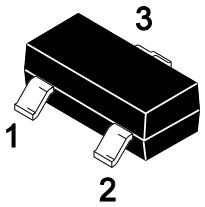
BAV70

Silicon Epitaxial Planar Switching Diode

Features

- Small package
- Low forward voltage
- Fast reverse recovery time

SOT-23

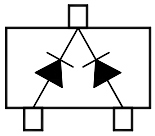


1.Anode1 2.Anode2
3.Cathode1、 Cathode2

Marking Code : A4

Equivalent Circuit

3.Cathode1、 Cathode2



1.Anode1 2.Anode2

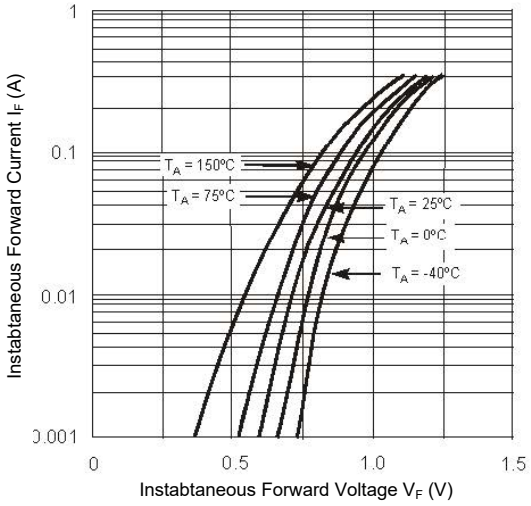
Absolute Maximum Ratings (T_A=25℃)

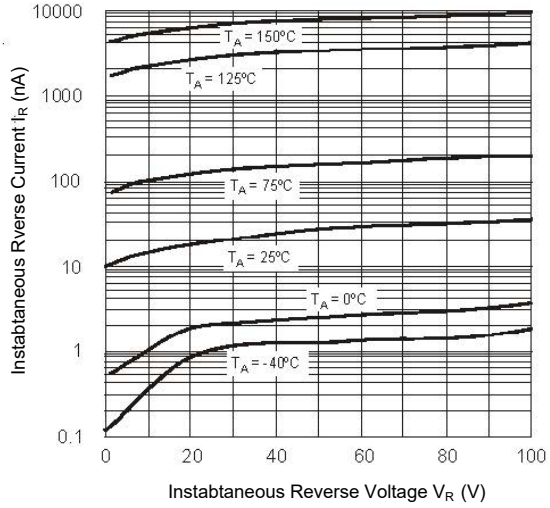
Parameter	Symbol	Value	Unit
Maximum Repetitive Reverse Voltage	V_{RRM}	100	V
Reverse Voltage	V_R	75	V
Average Rectified Forward Current	$I_{F(AV)}$	200	mA
Maximum Peak Forward Current	I_{FM}	300	mA
Non-repetitive Peak Forward Surge Current at t =1 s at t =1 μs	I_{FSM}	1 2	A
Power Dissipation	P_D	350	mW
Junction Temperature	T_J	150	°C
Storage Temperature Range	T_{STG}	-55 to +150	°C

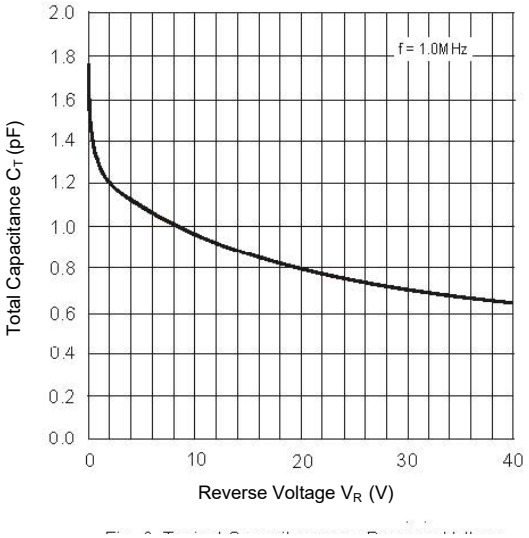
Electrical Characteristics (T_A=25℃)

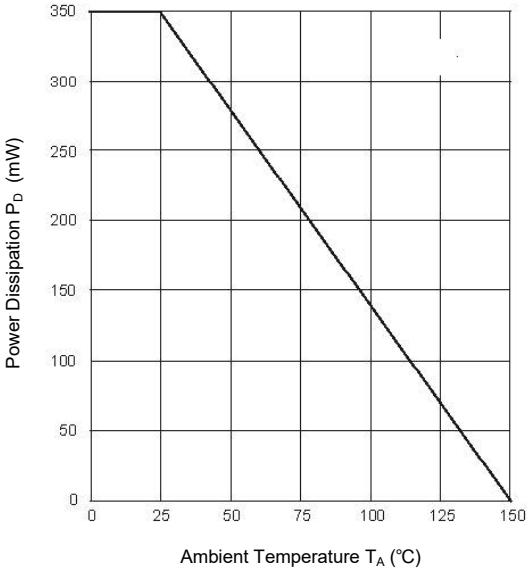
Parameter	Symbol	Min.	Max.	Unit
Forward Voltage at I_F = 1 mA at I_F = 10 mA at I_F = 50 mA at I_F = 150 mA	V_F	 -- -- -- --	 0.715 0.855 1 1.25	V
Reverse Breakdown Voltage at I_R = 100 μA	$V_{(BR)R}$	75	--	V
Reverse Current at V_R = 20 V at V_R = 75 V at V_R = 20 V, at T_J =150 °C at V_R = 75 V, at T_J =150 °C	I_R	 -- -- -- --	 0.025 2.5 30 50	μA
Typical Junction Capacitance at V_R= 0 V, f= 1 MHz	C_j	--	2	pF
Maximum Reverse Recovery Time at I_F = 10 mA, V_R = 6 V, I_{RR} = 1 mA, R_L = 100 Ω	T_{rr}	--	4	nS

Typical Characteristic Curves





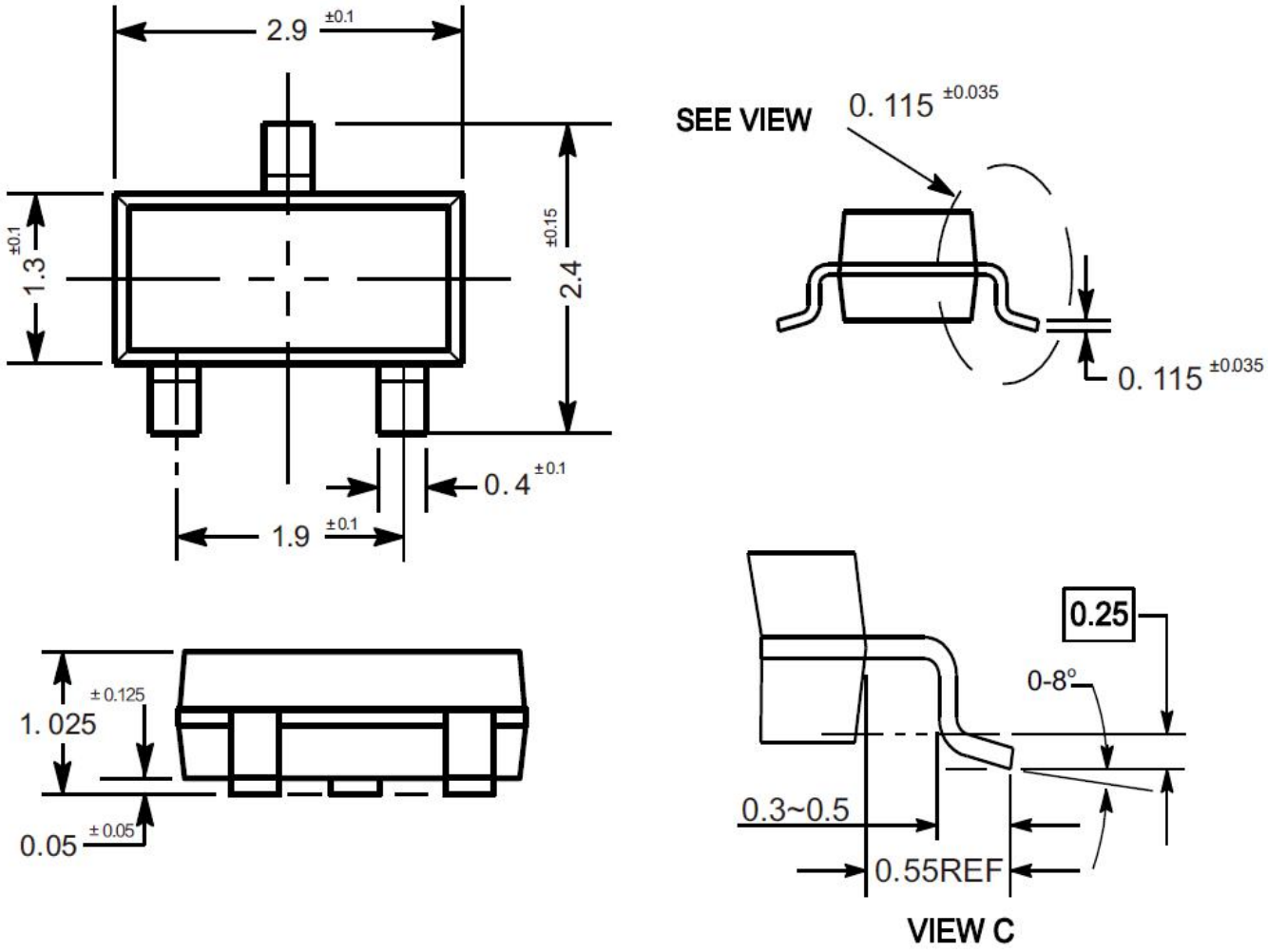




Package Outline

SOT-23

Dimensions in mm



Ordering Information

Device	Package	Shipping
BAV70	SOT-23	3,000PCS/Reel&7inches